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PRODUCTION METHOD FOR SILICON WAFER AND SILICON WAFER

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Inventor:

ABE TAKAO [JP]; AIHARA KEN [JP]; AKIYAMA SHOJI

[JP]; IGARASHI TETSUYA [JP]; QU WEIFENG [JP]; HAYAMIZU YOSHINORI [JP]; SAITO SHIGERU [JP]

Applicant:

SHINETSU HANDOTAI KK [JP]

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FIG. 1 1.02+00 1.06+04 1,06+03 1.05+02 1.06+01 1.05+00 .10 15 L EXTERNITIVAL CAYGEN OF

Abstract of EP1087041

A silicon wafer is produced by growing a silicon single crystal ingot having a resistivity of 100 OMEGA .cm or more and an initial interstitial oxygen concentration of 10 to 25 ppma by the Czochralski method, processing the silicon single crystal ingot into a wafer, and subjecting the wafer to an oxygen precipitation heat treatment so that a residual interstitial oxygen concentration in the wafer should become 8 ppma or less. A silicon wafer produced as described above shows little decrease in resistivity even after a heat treatment in device production etc. Further, if a silicon wafer is produced and heat-treated so that the wafer should have the above-defined initial interstitial oxygen concentration and residual interstitial oxygen concentration, slip dislocations in a subsequent heat treatment process are prevented irrespective of resistivity. Furthermore, by forming an epitaxial layer on a surface of a silicon wafer of the present invention, a high resistivity epitaxial wafer can be produced, which is free from slip dislocations etc. and can be used for various devices.

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